

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	100mΩ @ V _{GS} = -4.5V	-2.0A
	120mΩ @ V _{GS} = -2.5V	-1.9A
	160mΩ @ V _{GS} = -1.8V	-1.6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

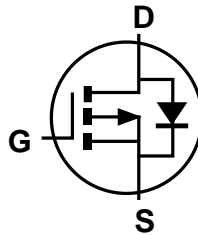
Applications

- Motor Control
- Power Management Functions
- Backlighting

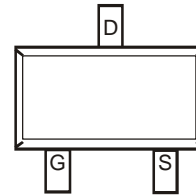
SOT323



Top View



Internal Schematic



Top View

Features and Benefits

- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

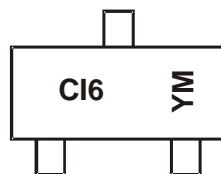
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208③
- Weight: 0.006 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110UW-7	SOT323	3000/Tape & Reel
DMP2110UW-13	SOT323	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



CI6 = Marking Code
 YM = Date Code Marking
 Y = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	F	G	H	I	J	K	L	M	N	O	P	R

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	T _A = +25°C	-2.0
Steady State		T _A = +70°C	-1.6
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-0.9	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)	I _{DM}	-15	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.49	W
Thermal Resistance, Junction to Ambient	R _{θJA}	253	°C/W
Total Power Dissipation (Note 6)	P _D	0.65	W
Thermal Resistance, Junction to Ambient	R _{θJA}	192	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100 ±800	nA	V _{GS} = ±8V, V _{DS} = 0V V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	—	-0.9	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	63	100	mΩ	V _{GS} = -4.5V, I _D = -1.5A
		—	75	120		V _{GS} = -2.5V, I _D = -1.2A
		—	89	160		V _{GS} = -1.8V, I _D = -1A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	443	—	pF	V _{DS} = -6V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	59	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	47	—	pF	
Gate Resistance	R _G	—	8.5	—	Ω	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	6.0	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -3A
Gate-Source Charge	Q _{gs}	—	0.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.8	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.0	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _G = 1.0Ω, I _D = -1A
Turn-On Rise Time	t _R	—	3.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	24.5	—	ns	
Turn-Off Fall Time	t _F	—	9.5	—	ns	
Reverse Recovery Time	t _{RR}	—	8.3	—	ns	I _F = -1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	2.0	—	nC	I _F = -1.0A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

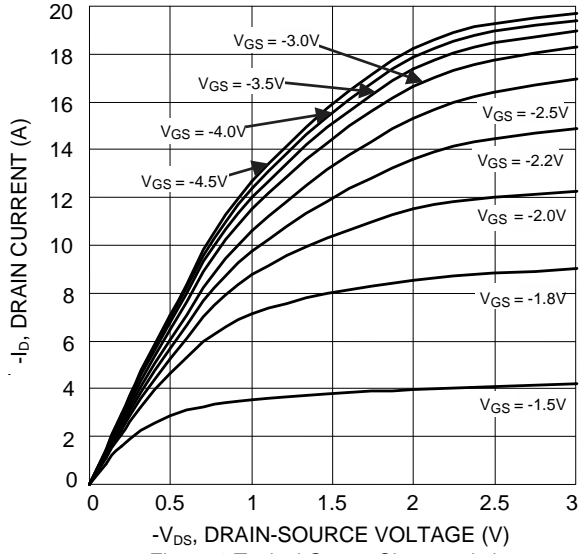


Figure 1 Typical Output Characteristics

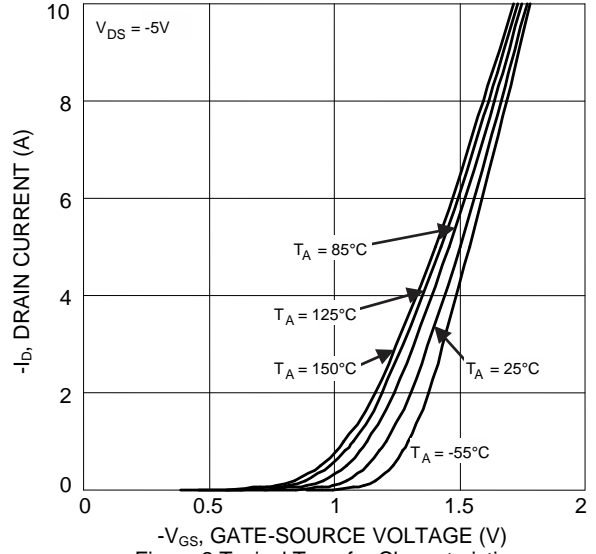


Figure 2 Typical Transfer Characteristics

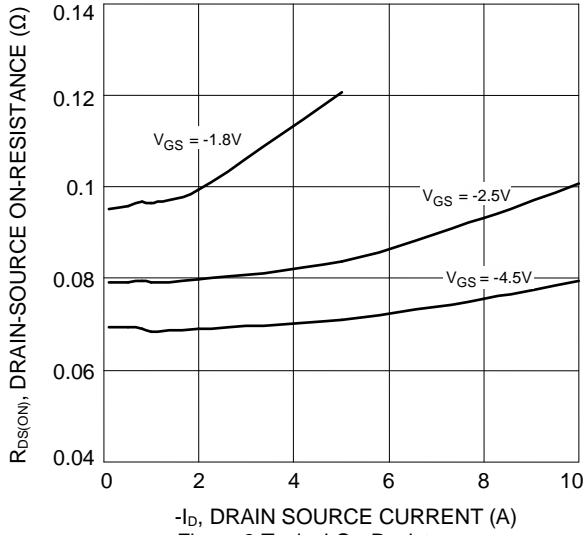


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

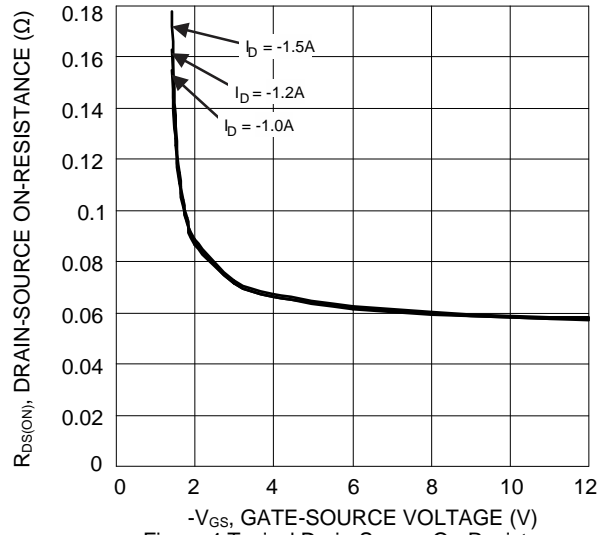


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

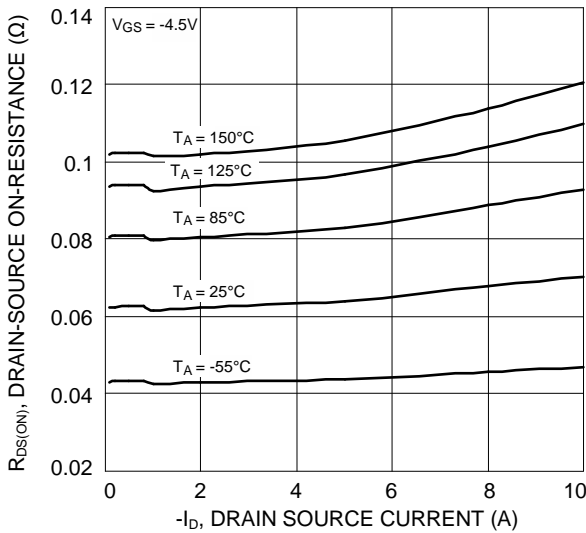


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

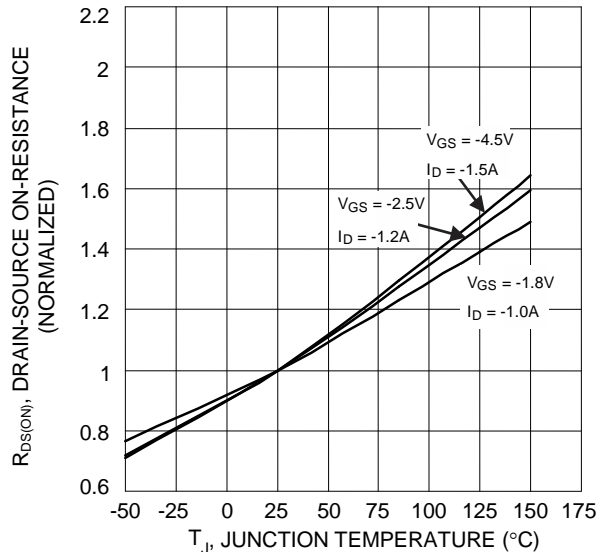


Figure 6 On-Resistance Variation with Temperature

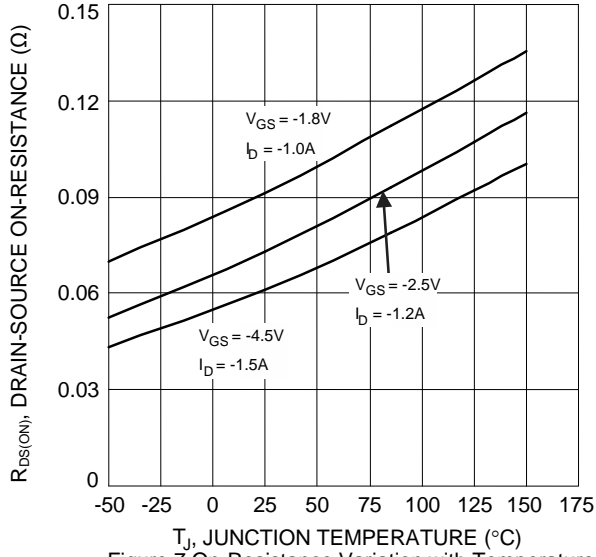


Figure 7 On-Resistance Variation with Temperature

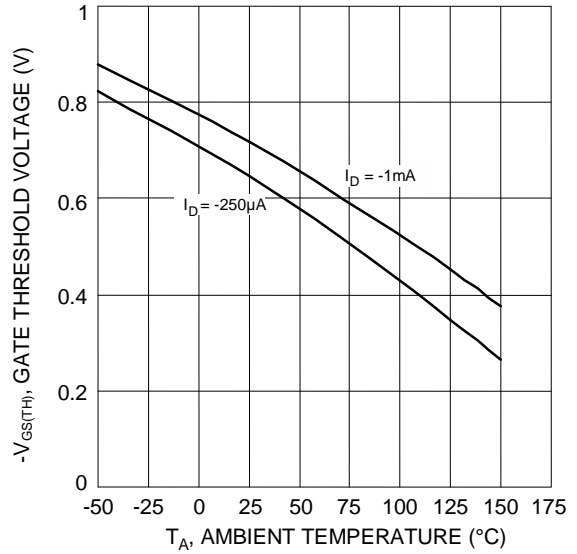


Figure 8 Gate Threshold Variation vs. Ambient Temperature

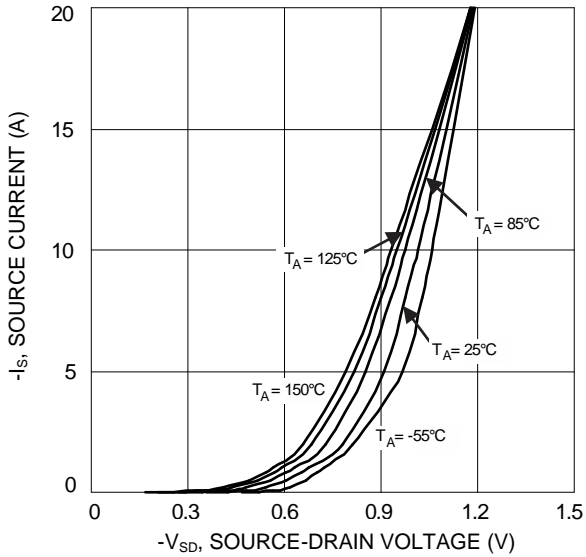


Figure 9 Diode Forward Voltage vs. Current

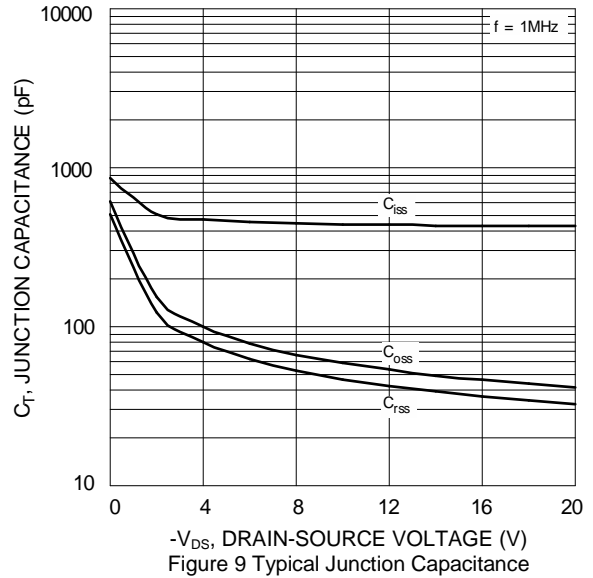


Figure 9 Typical Junction Capacitance

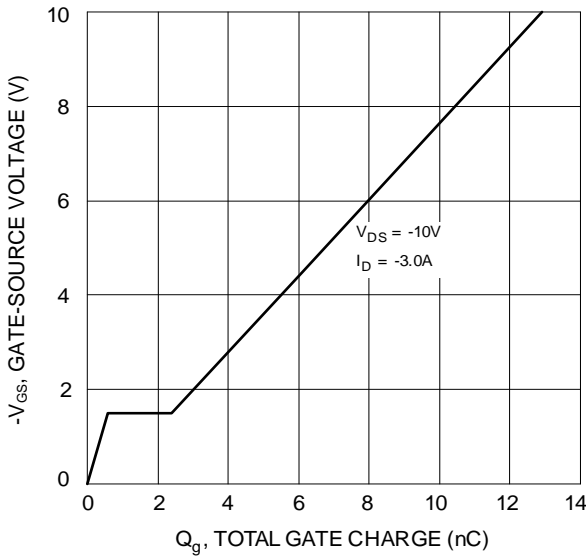


Figure 11 Gate Charge

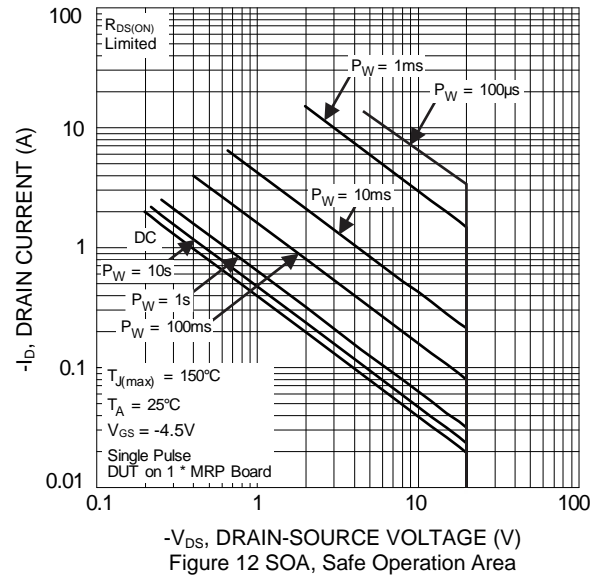
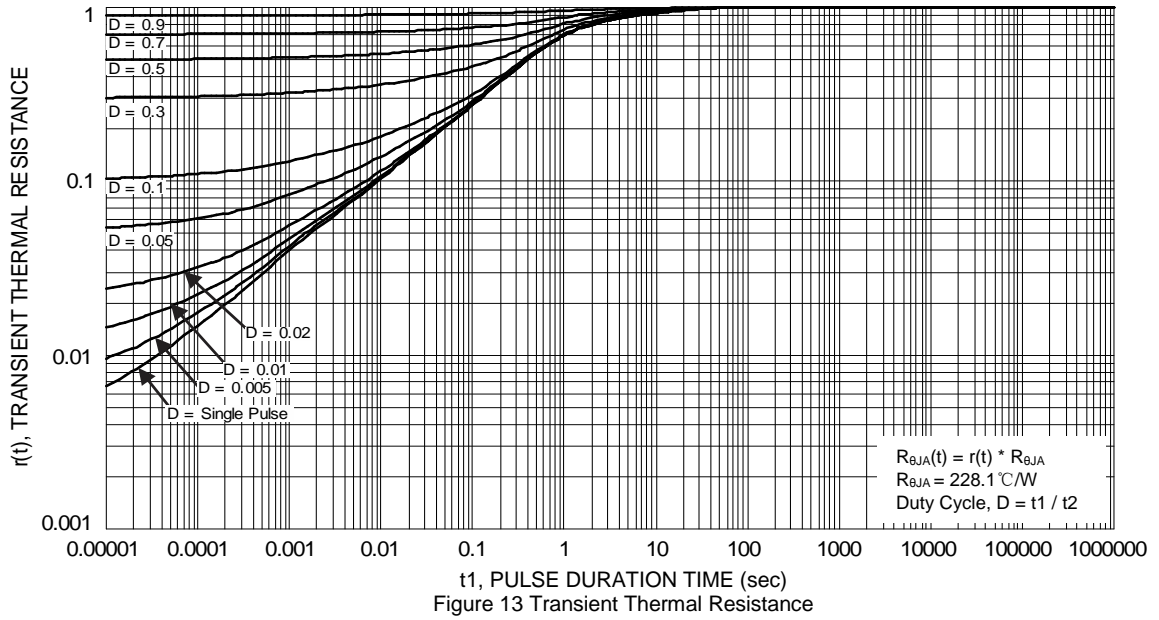


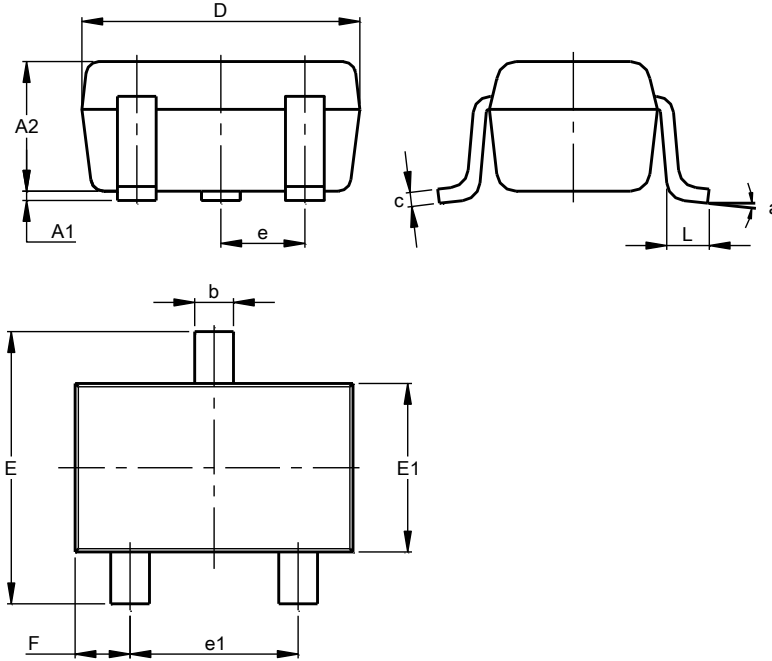
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323

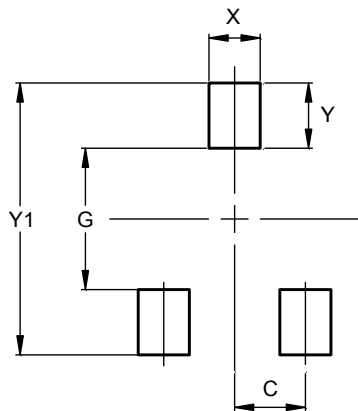


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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